METHOD AND APPARATUS FOR APPLYING DIFFERENTIAL REMOVAL RATES TO A SURFACE OF A SUBSTRATE

ABSTRACT OF THE DISCLOSURE

A semiconductor processing system is provided. The system includes a sensor configured to detect a signal representing a thickness of a film disposed on a surface of a substrate. A first nozzle configured to apply a first fluid to a surface of a polishing pad is included. A fluid restraining device located upstream from the first nozzle is provided. The fluid restraining device is configured to evenly distribute the slurry over the surface of the polishing pad. A second nozzle located upstream from the fluid restraining device is included. The second nozzle is configured to apply a second fluid to the evenly distributed slurry. A CMP system and a method for applying differential removal rates to a surface of a substrate are also provided.